Complementary Silicon Power Transistors

The 2N3773 and 2N6609 are PowerBase power transistors designed for high power audio, disk head positioners and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc to dc converters or inverters.

- High Safe Operating Area (100% Tested) 150 W @ 100 V
- Completely Characterized for Linear Operation
- High DC Current Gain and Low Saturation Voltage hFE = 15 (Min) @ 8 A, 4 V VCE(sat) = 1.4 V (Max) @ IC = 8 A, IB = 0.8 A
- For Low Distortion Complementary Designs

NPN 2N3773* PNP 2N6609

*Motorola Preferred Device

16 AMPERE
COMPLEMENTARY
POWER TRANSISTORS
140 VOLTS
150 WATTS



CASE 1-07 TO-204AA (TO-3)

*MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector Emitter Voltage	V _{CEO}	140	Vdc
Collector-Emitter Voltage	V _{CEX}	160	Vdc
Collector-Base Voltage	V _{CBO} 160		Vdc
Emitter-Base Voltage	V _{EBO}	7	Vdc
Collector Current — Continuous — Peak (1)	IC	16 30	Adc
Base Current — Continuous — Peak (1)	lΒ	4 15	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	150 0.855	Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta$ JC	1.17	°C/W

^{*} Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.

Preferred devices are Motorola recommended choices for future use and best overall value.



2N3773 2N6609

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (1)			•	•
*Collector–Emitter Breakdown Voltage $(I_C = 0.2 \text{ Adc}, I_B = 0)$	VCEO(sus)	140	_	Vdc
*Collector–Emitter Sustaining Voltage (I _C = 0.1 Adc, V _{BE(off)} = 1.5 Vdc, R _{BE} = 100 Ohms)	VCEX(sus)	160	_	Vdc
Collector–Emitter Sustaining Voltage (I _C = 0.2 Adc, R _{BE} = 100 Ohms)	VCER(sus)	150	_	Vdc
*Collector Cutoff Current (V _{CE} = 120 Vdc, I _B = 0)	ICEO	_	10	mAdc
*Collector Cutoff Current (V _{CE} = 140 Vdc, V _{BE} (off) = 1.5 Vdc) (V _{CE} = 140 Vdc, V _{BE} (off) = 1.5 Vdc, T _C = 150°C)	ICEX	_ _ _	2 10	mAdc
Collector Cutoff Current (V _{CB} = 140 Vdc, I _E = 0)	ICBO	_	2	mAdc
*Emitter Cutoff Current (VBE = 7 Vdc, I _C = 0)	^I EBO	_	5	mAdc
ON CHARACTERISTICS (1)			•	•
DC Current Gain *(I _C = 8 Adc, V _{CE} = 4 Vdc) (I _C = 16 Adc, V _{CE} = 4 Vdc)	hFE	15 5	60 —	_
Collector–Emitter Saturation Voltage *(I _C = 8 Adc, I _B = 800 mAdc) (I _C = 16 Adc, I _B = 3.2 Adc)	VCE(sat)	_ _	1.4 4	Vdc
*Base–Emitter On Voltage (I _C = 8 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	_	2.2	Vdc
DYNAMIC CHARACTERISTICS			•	
Magnitude of Common–Emitter Small–Signal, Short–Circuit, Forward Current Transfer Ratio (I _C = 1 A, f = 50 kHz)	h _{fe}	4	_	_
*Small-Signal Current Gain (I _C = 1 Adc, V _{CE} = 4 Vdc, f = 1 kHz)	h _{fe}	40	_	_
SECOND BREAKDOWN CHARACTERISTICS			-	•
Second Breakdown Collector Current with Base Forward Biased t = 1 s (non–repetitive), V _{CE} = 100 V, See Figure 12	I _{S/b}	1.5	_	Adc
				_

⁽¹⁾ Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%. * Indicates JEDEC Registered Data.

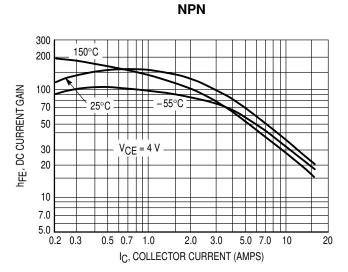


Figure 1. DC Current Gain

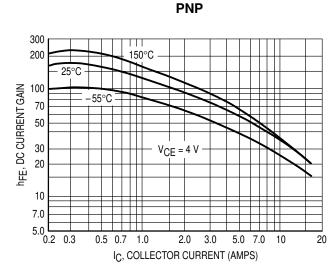


Figure 2. DC Current Gain

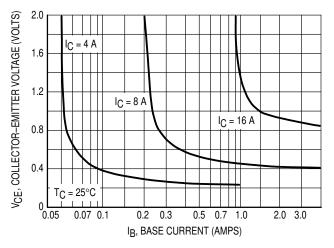


Figure 3. Collector Saturation Region

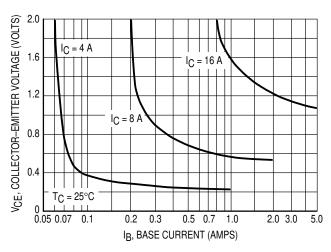


Figure 4. Collector Saturation Region

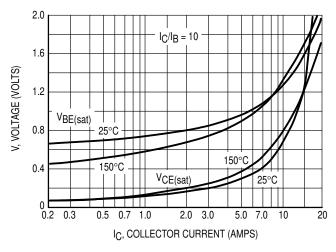


Figure 5. "On" Voltage

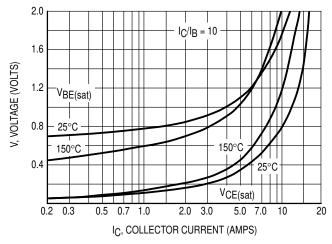


Figure 6. "On" Voltage

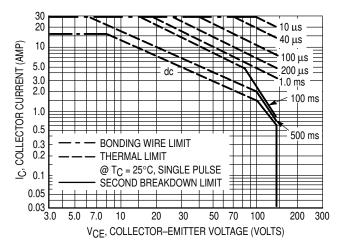


Figure 7. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation: i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 7 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 200^{\circ}C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

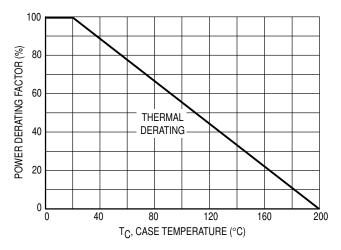
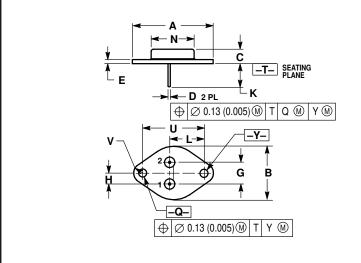


Figure 8. Power Derating

PACKAGE DIMENSIONS



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37 REF		
В	-	1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
E	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N	_	0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187 BSC		30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) ISSUE Z

2N3773 2N6609

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